NVHL160N120SC1

Silicon Carbide MOSFET, N-Channel, 1200 V, 160 mΩ, TO247-3L

Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- 1200V rated
- High Speed Switching and Low Capacitance
- Qualified for Automotive According to AEC-Q101

Benefits

- Blocking Voltage
- Coss = 50
- Devices are Pb-Free and are RoHS Compliant

Applications

- DC-DC Power
- On Board Charging

End Products

- EV/HEV

Part Electrical Specifications

Product	Pricing ($/Unit)	Compliance	Status	Family	Blocking Voltage BV_{DSS} (V)	$I_{D(max)}$ (A)	$R_{DS(on)}$ Typ @ 25°C (mΩ)	Q_g Total (nC)	Output Capacitance (pF)	T_j Max (°C)	Package Type
NVHL160N120SC1	4.224	A P Pb H	Active	M1	1200	26	160	24	40	175	TO-247-3LD